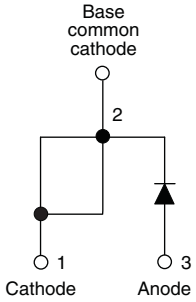
HEXFRED®
Ultrafast Soft Recovery Diode, 30 A



TO-247AC modified

FEATURES

- Ultrafast and ultrasoft recovery
- Very low I_{RRM} and Q_{rr}
- Compliant to RoHS Directive 2002/95/EC
- Designed and qualified for industrial level

Pb-free

e3

RoHS COMPLIANT

BENEFITS

- Reduced RFI and EMI
- Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- Reduced parts count

DESCRIPTION

VS-HFA30PB120PbF is a state of the art center tap ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 30 A continuous current, the VS-HFA30PB120PbF is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the t_b portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA30PB120PbF is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

PRODUCT SUMMARY	
Package	TO-247AC modified (2 pins)
$I_{F(AV)}$	30 A
V_R	1200 V
V_F at I_F	4.1 V
t_{rr} (typ.)	47 ns
T_J max.	150 °C
Diode variation	Single die

ABSOLUTE MAXIMUM RATINGS				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUES**	**UNITS**
Cathode to anode voltage	V_R		1200	V
Maximum continuous forward current	I_F	T_C = 100 °C	30	A
Single pulse forward current	I_{FSM}		120	
Maximum repetitive forward current	I_{FRM}		90	
Maximum power dissipation	P_D	T_C = 25 °C	350	W
		T_C = 100 °C	140	
Operating junction and storage temperature range	T_J, T_{Stg}		- 55 to + 150	°C

ELECTRICAL SPECIFICATIONS (T_J = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I_R = 100 µA		1200	-	-	V
Maximum forward voltage	V_{FM}	I_F = 30 A	See fig. 1	-	2.4	4.1	
		I_F = 60 A		-	3.1	5.7	
		I_F = 30 A, T_J = 125 °C		-	2.3	4.0	
Maximum reverse leakage current	I_{RM}	V_R = V_R rated	See fig. 2	-	1.3	40	µA
		T_J = 125 °C, V_R = 0.8 x V_R rated		-	1.1	4000	
Junction capacitance	C_T	V_R = 200 V	See fig. 3	-	50	75	pF
Series inductance	L_S	Measured lead to lead 5 mm from package body		-	8.0	-	nH

DYNAMIC RECOVERY CHARACTERISTICS (T_J = 25 °C unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time See fig. 5, 10	t_{rr}	I_F = 1.0 A, dI_F/dt = 200 A/µs, V_R = 30 V		-	47	-	ns
	t_{rr1}	T_J = 25 °C	I_F = 30 A dI_F/dt = 200 A/µs V_R = 200 V	-	110	170	
	t_{rr2}	T_J = 125 °C		-	170	260	
Peak recovery current See fig. 6	I_{RRM1}	T_J = 25 °C		-	10	15	A
	I_{RRM2}	T_J = 125 °C		-	16	24	
Reverse recovery charge See fig. 7	Q_{rr1}	T_J = 25 °C		-	650	980	nC
	Q_{rr2}	T_J = 125 °C		-	1540	2310	
Peak rate of fall of recovery current during t_b See fig. 8	$dI_{(rec)M}/dt1$	T_J = 25 °C		-	270	-	A/µs
	$dI_{(rec)M}/dt2$	T_J = 125 °C		-	240	-	

THERMAL - MECHANICAL SPECIFICATIONS

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T_{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R_{thJC}		-	-	0.36	°C/W
Thermal resistance, junction to ambient	R_{thJA}	Typical socket mount	-	-	80	
Thermal resistance, case to heatsink	R_{thCS}	Mounting surface, flat, smooth and greased	-	0.50	-	
Weight			-	2.0	-	g
			-	0.07	-	oz.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC modified (JEDEC)	HFA30PB120			

For technical questions within your region, please contact one of the following:
DiodesAmericas@vishay.com, DiodesAsia@vishay.com, DiodesEurope@vishay.com

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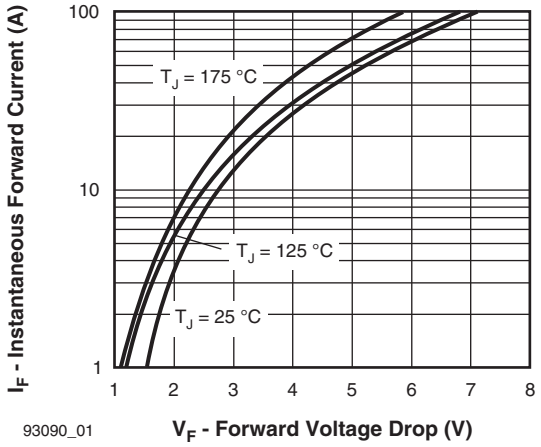

Fig. 1 - Typical Forward Voltage Drop vs. Instantaneous Forward Current

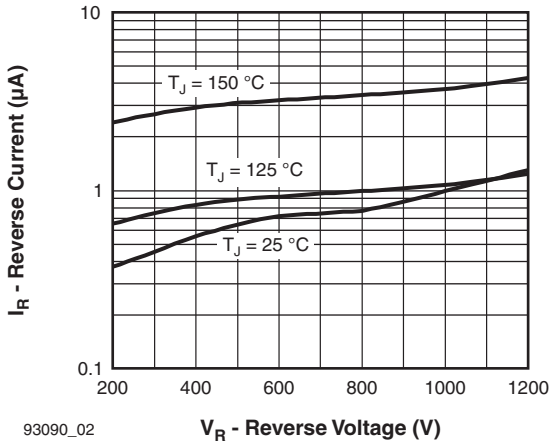

Fig. 2 - Typical Reverse Current vs. Reverse Voltage

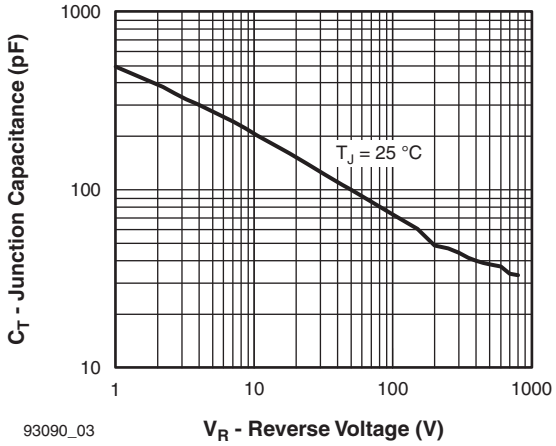

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

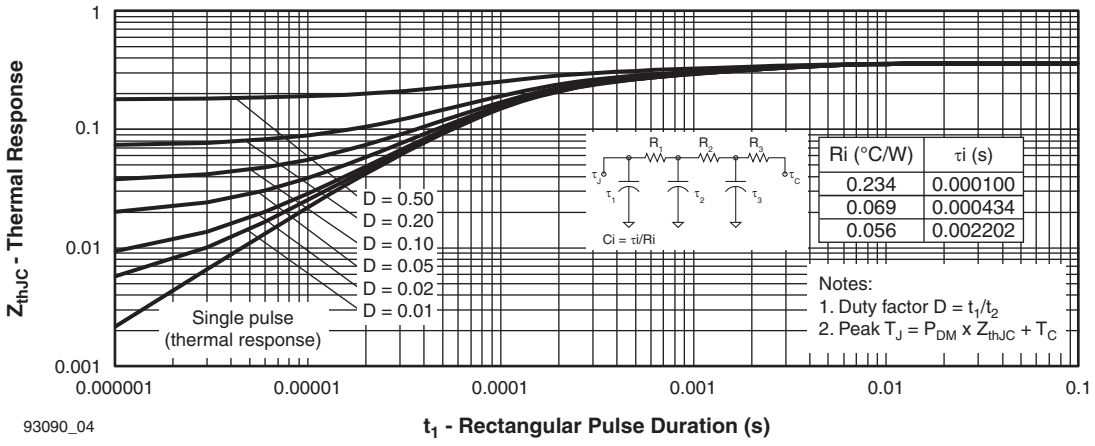

Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics

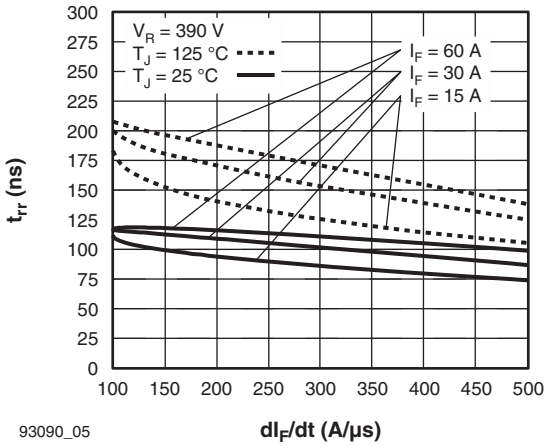

Fig. 5 - Typical Reverse Recovery Time vs. dI_F/dt (Per Leg)

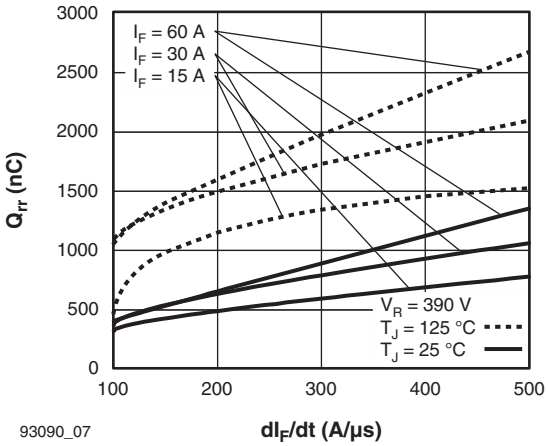

Fig. 7 - Typical Stored Charge vs. dI_F/dt (Per Leg)

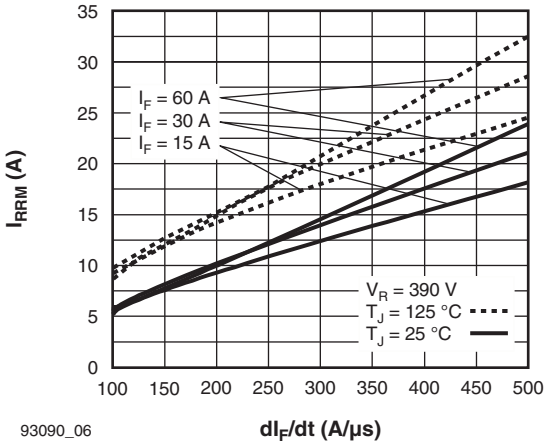

Fig. 6 - Typical Recovery Current vs. dI_F/dt (Per Leg)

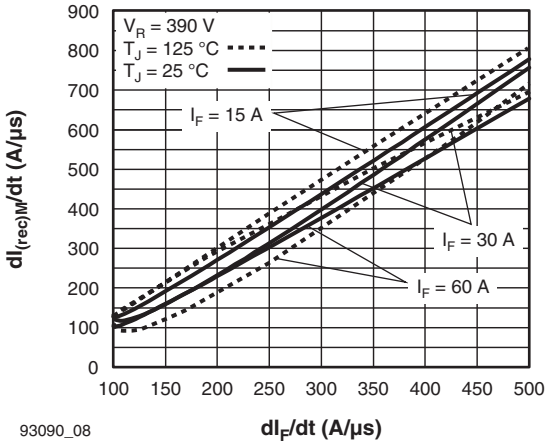

Fig. 8 - Typical $dI_{(rec)M}/dt$ vs. dI_F/dt(Per Leg)

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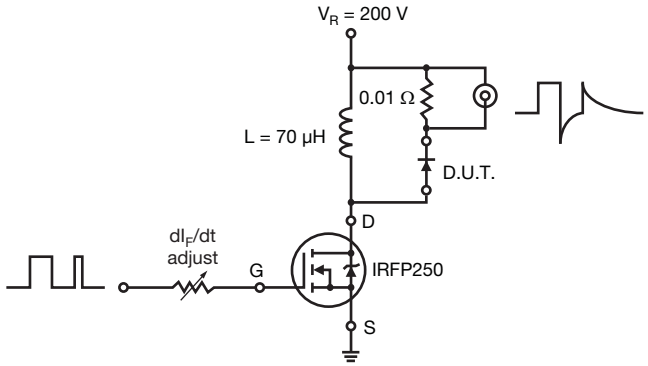
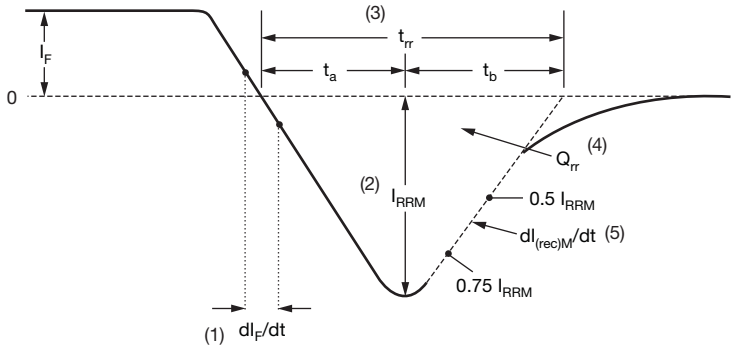


Fig. 9 - Reverse Recovery Parameter Test Circuit



(1) dI_F/dt - rate of change of current through zero crossing

(2) I_{RRM} - peak reverse recovery current

(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(4) Q_{rr} - area under curve defined by t_{rr} and I_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

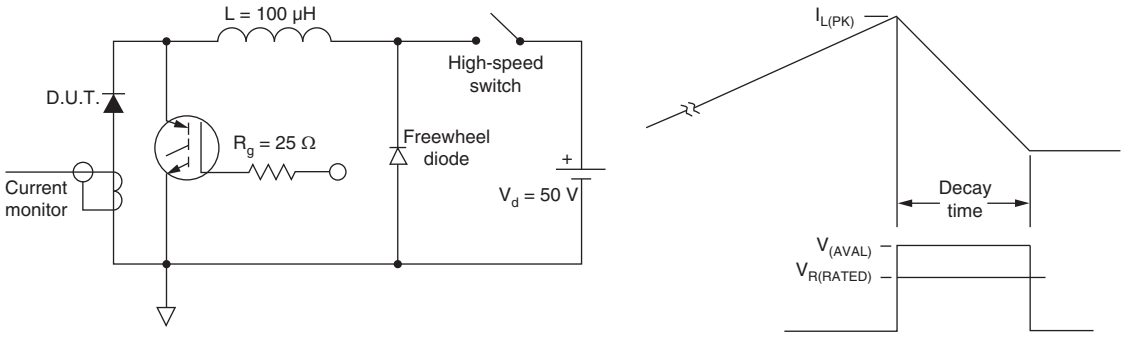
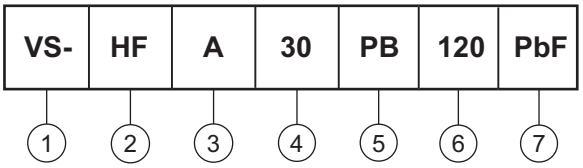


Fig. 11 - Avalanche Test Circuit and Waveforms

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product
2 - HEXFRED® family
3 - Electron irradiated
4 - Current rating (30 = 30 A)
5 - PB = TO-247AC modified
6 - Voltage rating: (120 = 1200 V)
7 - PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95253
Part marking information	www.vishay.com/doc?95255
SPICE model	www.vishay.com/doc?95358

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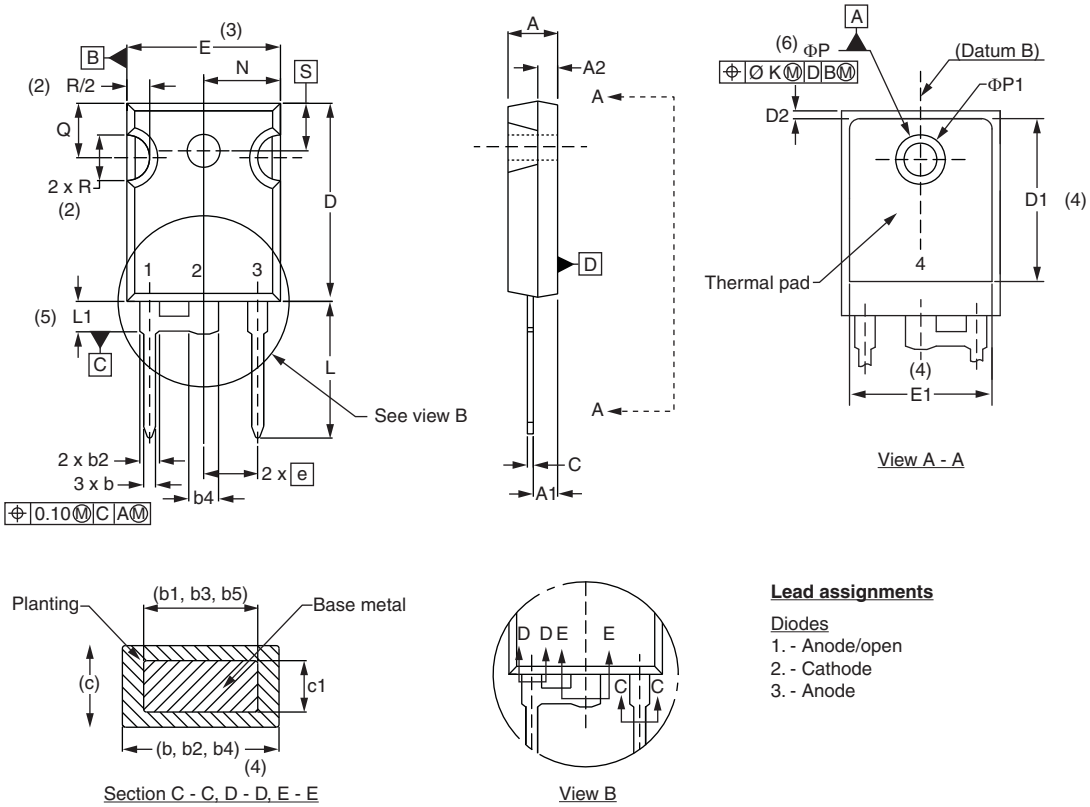
DIMENSIONS in millimeters and inches



Lead assignments

Diodes
1. - Anode/open
2. - Cathode
3. - Anode

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.65	5.31	0.183	0.209	
A1	2.21	2.59	0.087	0.102	
A2	1.50	2.49	0.059	0.098	
b	0.99	1.40	0.039	0.055	
b1	0.99	1.35	0.039	0.053	
b2	1.65	2.39	0.065	0.094	
b3	1.65	2.37	0.065	0.094	
b4	2.59	3.43	0.102	0.135	
b5	2.59	3.38	0.102	0.133	
c	0.38	0.86	0.015	0.034	
c1	0.38	0.76	0.015	0.030	
D	19.71	20.70	0.776	0.815	3
D1	13.08	-	0.515	-	4

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
D2	0.51	1.30	0.020	0.051	
E	15.29	15.87	0.602	0.625	3
E1	13.72	-	0.540	-	
e	5.46 BSC		0.215 BSC		
ΦK	2.54		0.010		
L	14.20	16.10	0.559	0.634	
L1	3.71	4.29	0.146	0.169	
N	7.62 BSC		0.3		
ΦP	3.56	3.66	0.14	0.144	
ΦP1	-	6.98	-	0.275	
Q	5.31	5.69	0.209	0.224	
R	4.52	5.49	1.78	0.216	
S	5.51 BSC		0.217 BSC		

Notes

(1) Dimensioning and tolerance per ASME Y14.5M-1994

(2) Contour of slot optional

(3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Thermal pad contour optional with dimensions D1 and E1

(5) Lead finish uncontrolled in L1

(6) ΦP to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

(7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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